example argon. A low temperature oxide passivated layer 12 is then deposited on wafer 10 adjacent Schottky contact 14. While it is believed that the Schottky barrier diode so fabricated has the requisite properties to function as required, the manufacturing process involves three lithographic masking steps to form contact 14, oxide layer 12, and edge termination 16 requiring the use of state-of-the-art equipment. The second and third mask applications require two alignment steps, and this method is thus time consuming and expensive.

B1

IN THE CLAIMS:

Please cancel claim 2 and amend claims 1, 3, 5 and 6 to read as shown. A complete set of claims 1, 3 – 8 and new claims 18 – 20 are presented below in clean version.

1. (Amended) A method for the fabrication of a Schottky barrier diode on a SiC wafer, comprising the steps of:

(a) forming an insulating layer on the surface of the SiC wafer;

(b) placing a mask having a window on an exposed surface of the insulating layer;

B2 SUB C' Cont.

(c) etching away a portion of the insulating layer corresponding to the window to expose a portion of the SiC wafer therebeneath;

(d) while retaining the mask in place, depositing conductive material on the mask and exposed portions of the wafer surface; and

(e) stripping off the mask so as to leave the conductive material